



dRICH SiPM news

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ePIC TIC meeting, 13 May 2024

Neutron fluxes at the dRICH photosensor surface

1-MeV neutron equivalent fluence (1 fb⁻¹ ep running)



assume fluence: ~ 10^7 neg / cm² / fb⁻¹ conservatively assume max fluence and 10x safety factor \rightarrow radiation damage studied in steps of radiation load 10^9 1-MeV n_{eq}/cm² most of the key physics topics 10¹⁰ 1-MeV n_{eq}⁴/cm² should cover most demanding measurements 10¹¹ 1-MeV n_{eo}³/cm² might never be reached



updated radiation simulations

New radiation damage estimates





xy projections in 210 < z < 260 cm region, average and max values reported for 100 < R < 180 cm region

New radiation damage estimates





before: max fluence = 9.2 10^5 neq/fb⁻¹ | now: max fluence = 1.75 10^7 neq/fb⁻¹ \Rightarrow new estimates are ~20x larger

New radiation damage estimates





new estimates are ~20x larger, but we had a 10x safety factor \Rightarrow we got the safety factor eaten and a 2x faster ageing

Updated ageing model



model input from R&D measurements (up to 2022)

- DCR increase: 500 kHz/10⁹ n_{en}
- residual DCR (online annealing): 50 kHz/10⁹ n_{eq}
- residual DCR (oven annealing): 15 kHz/10⁹ n_{eq}
- 1-MeV neq fluence from background group
 - 1.75 10⁷ n_{eq} / fb⁻¹
 - includes 2x safety factor

all parameters are the same used for the previous model only neq/fb⁻¹ is updated to new estimate, with 2x safety factor which corresponds to a 4x faster ageing than previously reported



test on a large number of proton irradiated sensors how much damage is cured as a function of temperature and time

in this study, the same sensors have undergone self-annealing in increasing temperature steps and increasing integrated time steps

- started with T = 100 C annealing
 performed 4 steps up to 30 hours integrated
- followed by T = 125, 150 and 175 C





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fraction of residual damage seems to saturate at 2-3% after ~ 300 hours at T = 150 C continuing at higher T = 175 C seems

not to cure more than that





but, after many hours of online annealing

we noticed alterations on the SiPM windows in particular in one board that underwent

500 hours of online annealing at T = 175 C

the sensors appear "yellowish" when compared to new

less "yellowish" but still a bit "yellowish" the sensors in a board that underwent 500 hours at T = 150 C

let's compare them under the laser light







25% efficiency loss after 500 h online at 150 C no efficiency loss after 500 h oven at 150 C

not clear why oven annealing is less critical on window, but in line with previously-reported "no damages due to annealing procedure" for 200 h in oven at T = 150 C



Light response after irradiation and annealing



window damage studies

Detailed studies of SiPM window damage



measurements are ongoing

- 4 SiPM under study
- each undergoing online annealing
 - at forward bias
 - at different temperature
 - following the same annealing protocol
 - same integrated annealing time and cycles

measurements are performed with the upgraded laser setup

the plot reports the variation of the PDE wrt. the sensors measured before the beginning of the annealing cycles (new)

measurements are still ongoing so far, after ~135 hours (135 1-hour cycles)

observation of beginning of efficiency loss at 175 C lower temperatures are unaffected

we will continue this study this is already good news





studies with laser

Comparison between sensors

3 Hamamatsu sensor types, 4 sensors each measured as NEW



proxy for photodetection efficiency

at the same level of detection efficiency

namely, the probability to detect light from laser pulse different sensors have different DCR level

best: S13360-3075

most promising sensors, large pitch SPADs (75 μ m) second: S13360-3050

same technology, medium pitch SPADs (50 μm) worst: S14160-3050

different technology, medium pitch SPADs (50 µm)

New Hamamatsu SiPM prototypes





newly-developed Hamamatsu SiPM sensors

based on S13360 series few samples of 50 μm and 75 μm SPAD sensors

on paper they look VERY promising

- improved NUV sensitivity
- improved signal shape
- improved recharge time

mounted on EIC SiPM test boards we will characterise and test them in full irradiation, annealing, laser, ...



800

prototype Hamamatsu sensors (10⁹ neq after oven annealing)



prototype Hamamatsu UVE sensors have significantly higher efficiency than standard sensors caveat: we only measure PDE at the fixed laser wavelength of ~400 nm, larger PDE expected because... prototype sensors have a NUV-enhanced behaviour.

we will study them further, currently asking Hamamatsu status for production and quotation of this product



Summary

• updated radiation simulations

- new radiation damage estimates at dRICH SiPM location
- a factor 20x larger than what reported last year
- dRICH used a 10x safety factor, the updated did no hurt too much
 - still this is not a good news, detector will age faster than expected so far

• detailed studies of online "in-situ" annealing

- o forward-bias annealing is better that reverse-bias (although current is higher)
- long forward-bias annealing can reach oven-annealing level of recovery
 - this is a pretty a good news
- but we observed degradation of efficiency / optical properties (likely the protective resin)
 - this sounds like a bad news, but
 - promising studies ongoing, T = 150 C annealing is effective and not destructive

Hamamatsu prototype SiPM sensors

- NUV and signal enhanced, very promising on paper
- \circ ~ laser studies show that they are indeed promising
 - we will study more, queried Hamamatsu for production / costs
 - this is a good news